

Application No.: 09/998,134
Art Unit 2823

Attorney Docket No. 2332-0117P
Page 3

Claim 1. (Amended)

A method for forming a junction in a semiconductor device with symmetrical halo implants, comprising the steps of:

forming a photoresist film pattern on a semiconductor substrate excluding a first region;

forming symmetrical first and second implants by performing a first halo implant process and a second halo implant process on the first region of the semiconductor substrate by using a tilt angle of about 45° and twist angles of 0° and 180° corresponding to the first halo implant and second halo implant, respectively; and

performing a third halo implant process on the first region of the semiconductor substrate by using a tilt angle of about 0°.

Claim 2. (Amended)

The method according to claim 1, wherein both the first halo implant process and second halo implant process are performed with an energy of 20KeV and a dose of 4.0×10^{12} ions/cm².

Claim 4. (Amended)

The method according to claim 1, wherein the third halo implant process is performed only once at a tilt angle of about 0°.

Application No.: 09/998,134
Art Unit 2823

Attorney Docket No. 2332-0117P
Page 4

C2
C4
C6
Claim 5. (Amended)

The method according to claim 1, wherein the third halo implant
process is performed with an energy of 16KeV and a dose of 4×10^{12} ions/cm².

Claim 8. (Amended)

A method for forming a junction with symmetrical halo implants in a semiconductor device, comprising the steps of:

providing a semiconductor substrate divided into a first conductive type MOS region and a second conductive type MOS region;

forming a photoresist film pattern on the second conductive type MOS region;

forming symmetrical first and second halo implants by performing first and second halo implant processes on the first conductive type MOS region at about a 45° tilt angle and at twist angles of about 0° and 180°, respectively; and

performing a third halo implant process on the first conductive type MOS region, by using a tilt angle of about 0°.

Claim 9. (Amended)

The method according to claim 8, wherein the first halo implant process is performed with an energy of 20KeV and a dose of 4.0×10^{12} ions/cm².

Application No.: 09/998,134
Art Unit 2823

Attorney Docket No. 2332-0117P
Page 5

Claim 10. (Amended)

B5
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The method according to claim 8, wherein the second halo implant process is performed with an energy of 20KeV and a dose of 4.0×10^{12} ions/cm².

Claim 11. (Amended)

The method according to claim 8, wherein the third halo implant process is performed with an energy of 16KeV and a dose of 4×10^{12} ions/cm².

Please add the following new claims:

B6
--14. The method of claim 1, wherein the first and second halo implants are homogenously doped.

15. The method of claim 8, wherein the first and second halo implants are homogenously doped.--
